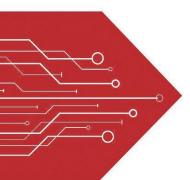
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Product data sheet

www.msksemi.com





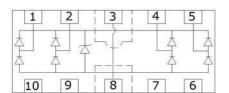


Features

- 150 Watts peak pulse power (tp = $8/20\mu s$)
- Transient protection for high speed data lines to IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact) IEC 61000-4-4 (EFT) 40A (5/50ns)
- Working voltages: 3.3V
- ◆ Protects two or four I/O lines
- Ultra Low capacitance:0.3pf (typical between I/O channel)
- Low operating and clamping voltages
- Solid-state silicon avalanche technology

Applications

- High Definition Multi-Media Interface (HDMI)
- USB 1.1/2.0/3.0/OTG
- IEEE 1394 Firewire Ports
- Projection TV Monitors and Flat Panel Displays
- **Notebook Computers**
- Set Top Box





DFN2510

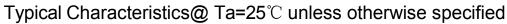
Maximum Rating @ Ta=25°C unless otherwise specified

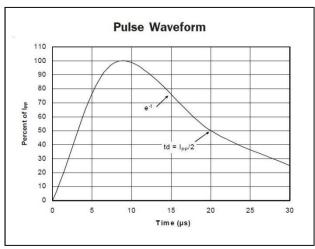
Symbol	Parameter	Ratings	Units
P _{PK}	Peak Pulse Power (tp = 8/20μs)	150	Watts
TL	Lead Soldering Temperature	260(10sec.)	$^{\circ}$
TJ	Operating Temperature	-55 to +125	$^{\circ}$ C
T _{STG}	Storage Temperature	-55 to +150	$^{\circ}$

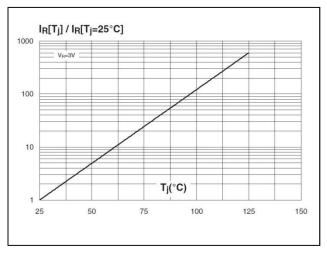
Electrical Characteristics@ Ta=25°C unless otherwise

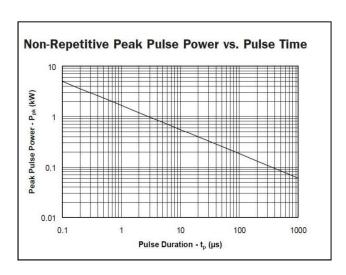
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V_{RWM}	Reverse Working Voltage	Any I/O to Ground		3.3		V
V _{BR}	Reverse Breakdown Voltage	I_T = 1mA, Any I/O to Ground	4.5			V
I _R	Reverse Leakage Current	V_{RWM} = 5V, Any I/O to Ground			1	μΑ
V _F	Diode Forward Voltage	I _F = 15mA		0.85	1.2	V
Vc	Olamania a Malka a a	I_{PP} = 1A, tp =8/20µs, any I/O pin to Ground			9.8	V
	Clamping Voltage	I _{PP} = 5A, tp =8/20µs, any I/O pin to Ground			15	V
СJ	Junation Canacitanes	V _R = 0V, f = 1MHz, between I/O pins		0.25	0.3	pF
	Junction Capacitance	V_R = 0V, f = 1MHz, any I/O pin to Ground		0.5	0.6	pF

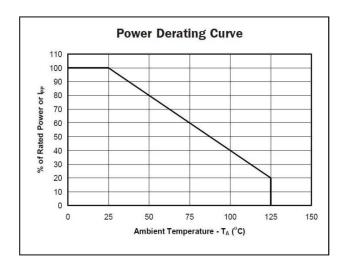






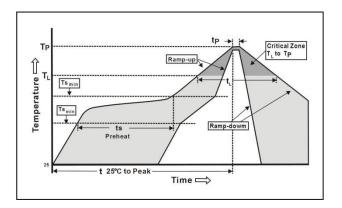






Soldering Parameters

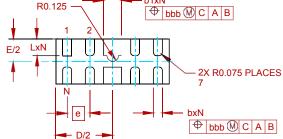
Reflow Co	endition	Fb — Free assembly	
	-Temperature Min (T _{s(Min)})	150°C	
Pre Heat	- Temperature Max (T _{s(Max)})	200°C	
	-Time (Min to max) (t _s)	60 – 180 secs	
Average r (T _L) to pea	amp up rate (Liquidus) Temp k	3°C/second Max	
T _{s (Max)} to T _L - Ramp-up Rate		3°C/second Max	
Reflow	-Temperature (T _L) (Liquidus)	217°C	
Kellow	-Temperature (t _L)	60 – 150 seconds	
Peak Tem	perature (T _p)	250+0/-5 °C	
Time within 5°C of actual peak Temperature (t _p)		20 – 40 seconds	
Ramp-dowm Rate		6°C/second Max	
Time 25°C to peak Temperature (T _p)		8 minutes Max.	
Do not ex	ceed	260°C	



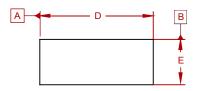


PACKAGE MECHANICAL DATA



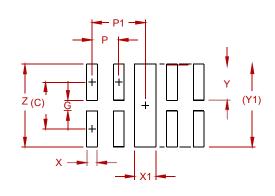


Dimensions in millimeters



DIMENSI ONS						
DIM	INC	HES	MILLIMETERS			
J	MIN	NOM	MAX	MIN	NOM	MAX
Α	.020	.023	.026	0.50	0.58	0.65
A1	0.00	.001	.002	0.00	0.03	0.05
A2	(.005)			(0	(0.13)	
b	.006	.008	.010	0.15	0.20	0.25
b1	.014	.016	.018	0.35	0.40	0.45
D	.094	.098	.102	2.40	2.50	2.60
E	.035	.039	.043	0.90	1.00	1.10
е	.020 BSC			0.50 BSC		
L	.012	.015	.017	0.30	0.38	0.425
N	8		8			
aaa	.003		0.08			
bbb		.004		0.10		

Suggested Pad Layout



DIMENSIONS			
DIM	INCHES	MILLIMETERS	
С	(.034)	(0.875)	
G	.008	0.20	
Р	.020	0.50	
P1	.039	1.00	
Х	.008	0.20	
X1	.016	0.40	
Υ	.027	0.675	
Y1	(.061)	(1.55)	
Z	.061	1.55	

NOTES:

CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES). THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
AZ9143-04F-MS	DFN2510	3000

Semiconductor

Compiance

Attention

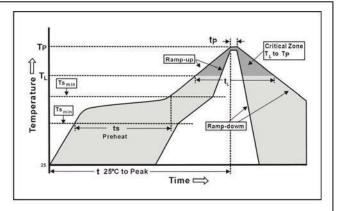
- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.



Transient Voltage Suppressors for ESD Protection

Soldering Parameters

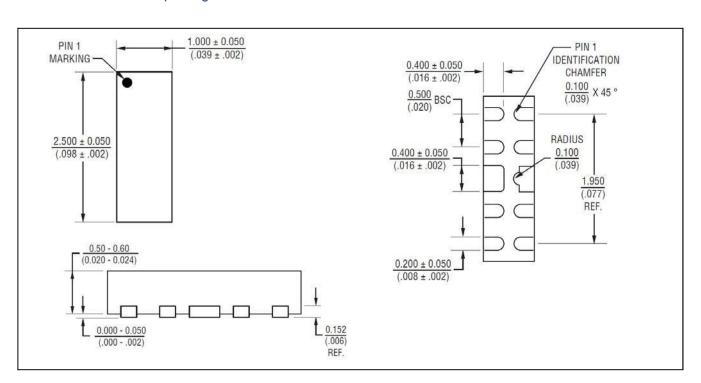
Reflow Condition		Fb – Free assembly	
	-Temperature Min (T _{s(Min)})	150°C	
Pre Heat	- Temperature Max (T _{s(Max)})	200°C	
	-Time (Min to max) (t _s)	60 - 180 secs	
Average r (T _L) to pea	ramp up rate (Liquidus) Temp ak	3°C/second Max	
T _{s (Max)} to T	- Ramp-up Rate	3°C/second Max	
Reflow	-Temperature (T _L) (Liquidus)	217°C	
	-Temperature (t _L)	60 – 150 seconds	
Peak Tem	perature (T _p)	250+0/-5 °C	
Time within 5°C of actual peak Temperature (t _p)		20 – 40 seconds	
Ramp-dowm Rate		6°C/second Max	
Time 25°C to peak Temperature (T _p)		8 minutes Max.	
Do not exceed		260°C	



Package Outline

Plastic surface mounted package

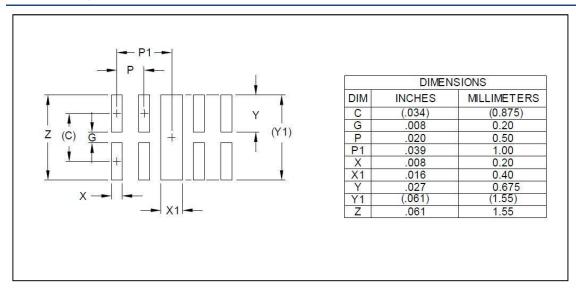
DFN2510





Transient Voltage Suppressors for ESD Protection

Soldering Footprint



Package And Marking Information

Device	Package	Shipping	Reel Size
TAPING	DFN2510	3000/Reel	7 inch

单击下面可查看定价,库存,交付和生命周期等信息

>>MSKSEMI (美森科)